

## Product Overview

### NGTB20N135IHR: IGBT 1350V 20A FS2-RC Induction Heating

For complete documentation, see the data sheet.



This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS)Trench construction, and provides superior performance in demanding switching applications, offering both low on-state voltage and minimal switching loss. The IGBT is well suited for resonant or soft switching applications.

### Features

- Optimized for Low Case Temperature in IH Cooker Applications
- Extremely Efficient Trench with Fieldstop Technology
- 1350V Breakdown Voltage
- Reliable and Cost Effective Single Die Solution

### Benefits

- Low Switching Loss Reduces System Power Dissipation

### Applications

- Inductive Heating
- Consumer Appliances
- Soft Switching

### Part Electrical Specifications

Product	Compliance	Status	$V_{ES}^{(BR)C}$ Typ (V)	$I_C$ Max (A)	$V_{CE(sat)}$ Typ (V)	$V_F$ Typ (V)	$E_{off}$ Typ (mJ)	$E_{on}$ Typ (mJ)	$T_{rr}$ Typ (ns)	$I_{rr}$ Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand ( $\mu$ s)	$E_{AS}$ Typ (mJ)	$P_D$ Max (W)	Co- Pack aged Diode	Pack age Type
NGTB20N135IHRWG	Pb-free	Active	1350	20	2.2	1.8	0.6	-	-	-	234	-	-	394	Yes	TO-247-3
	Halide free															

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